

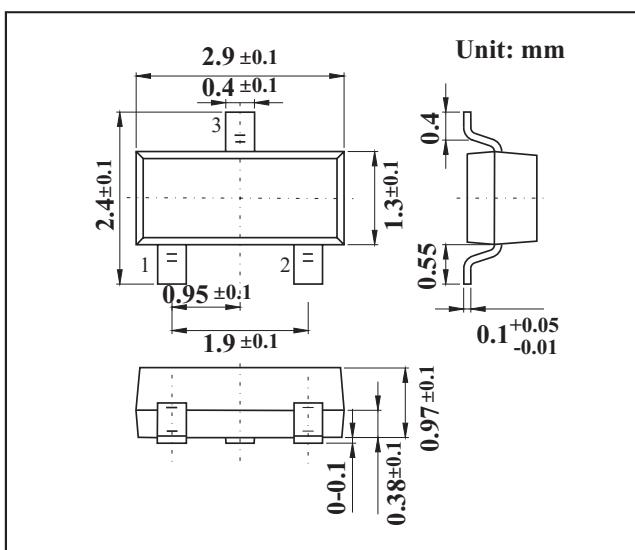
## SOT-23 Plastic-Encapsulate MOSFETS

## Features

- $V_{DS} = -30V$ ,  $r_{DS(on)} = 0.080\Omega$ ,  $V_{GS} = -10V$ ,  $ID = -3A$
  - $V_{DS} = -30V$ ,  $r_{DS(on)} = 0.140\Omega$ ,  $V_{GS} = -4.5V$ ,  $ID = -2.5A$
  - P-Channel 30-V (D-S) MOSFET

## **MECHANICAL DATA**

- Case style:SOT-23molded plastic
  - Mounting position:any



## **MAXIMUM RATINGS AND CHARACTERISTICS**

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V <sub>DS</sub>	-30	V
Gate-Source Voltage	V <sub>GС</sub>	±20	V
Continuous Drain Current TA=25°C TA=70°C	I <sub>D</sub>	-3 -2.5	A
Pulsed Drain Current *	I <sub>DM</sub>	-12	A
Power Dissipation TA=25°C TA=70°C	P <sub>D</sub>	1.25 0.8	W
Maximum Junction-to-Ambient *	R <sub>thJA</sub>	130	°C/ W
Junction Temperature,Storage Temperature	T <sub>j</sub> ,T <sub>stg</sub>	-55 to 150	°C

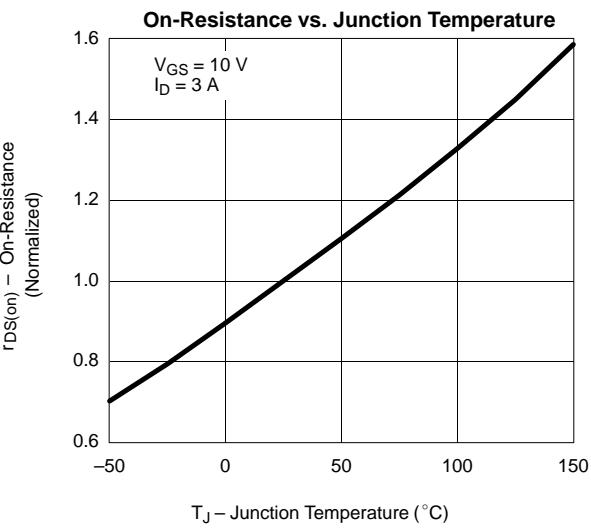
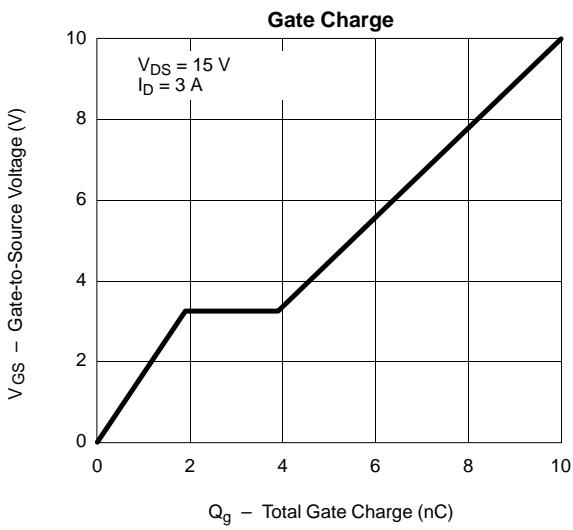
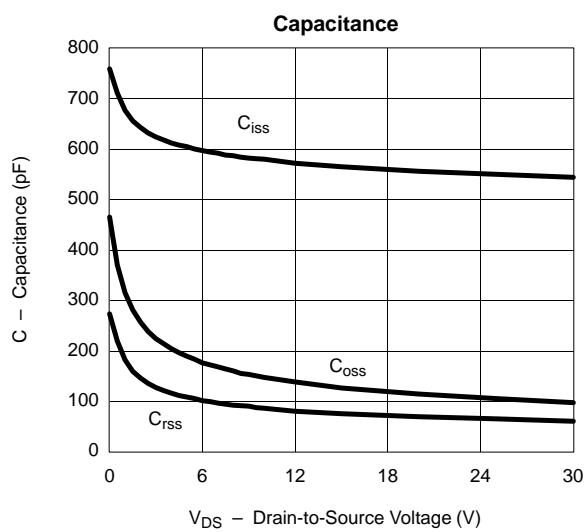
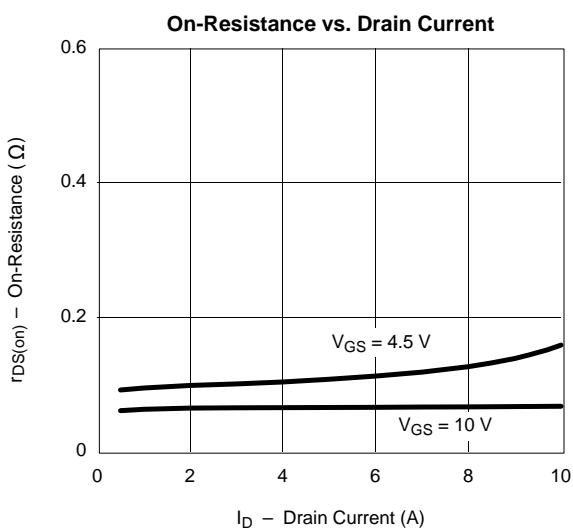
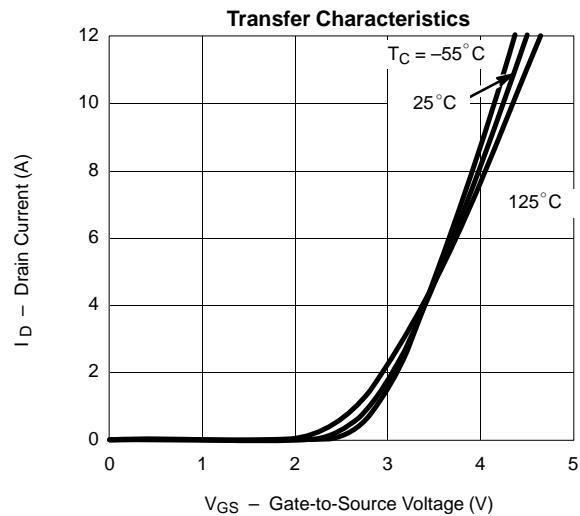
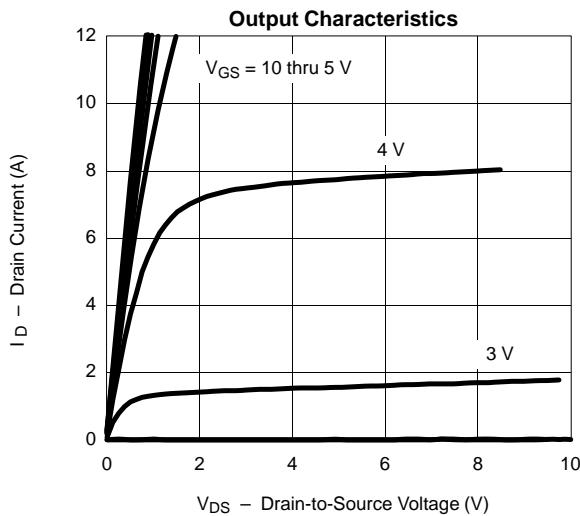
\* . Pulse width limited by maximum junction temperature

## MOSFET ELECTRICAL CHARACTERISTICS $T_a=25\text{ }^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	VDSS	VGS = 0 V, ID = -10 mA	-30			V
Zero Gate Voltage Drain Current	IDSS	VDS = -24 V, VGS = 0 V			-1	$\mu A$
		VDS = -24 V, VGS = 0 V, TJ = 55 °C			-10	
Gate-Body Leakage	IGSS	VDS = 0 V, VGS = ± 20 V			±100	nA
Gate Threshold Voltage	VGS(th)	VDS = VGS, ID = -250 mA	-1.0			V
Drain-Source On-State Resistance *	RDS(on)	VGS = -10 V, ID = -3 A		0.064	0.080	$\Omega$
		VGS = -4.5 V, ID = -2.5 A		0.103	0.140	
On-State Drain Current	ID(on)	VDS ≤ -5 V, VGS = -10 V	-6			A
Forward Transconductance *	gfs	VDS = -10 V, ID = -3 A		4.5		S
Input Capacitance	Ciss	VDS = -15 V, VGS = 0, f = 1 MHz		565		pF
Output Capacitance	Coss			126		
Reverse Transfer Capacitance	Crss			75		
Total Gate Charge	Qg	VDS = -15V ,VGS = -10 V , ID= -3A		10	15	nC
Gate-Source Charge	Qgs			1.9		
Gate-Drain Charge	Qgd			2		
Turn-On Time	td(on)	VDD=-15V,RL=15Ù, ID=-1A, VGEN=-10V,RG=6Ù		10	20	ns
	tr			9	2	
Turn-Off Time	td(off)			27	90	
	tf			7	1	
Continuous Source Current (diode conduction)	IS			-1.25	6	A
Diode Forward Voltage *	VSD	IS = -1.25 A, VGS = 0 V			-1.2	V

\* Pulse test: PW  $\leq 300$ μs duty cycle  $\leq 2\%$ .

## RATINGS AND CHARACTERISTIC CURVES



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